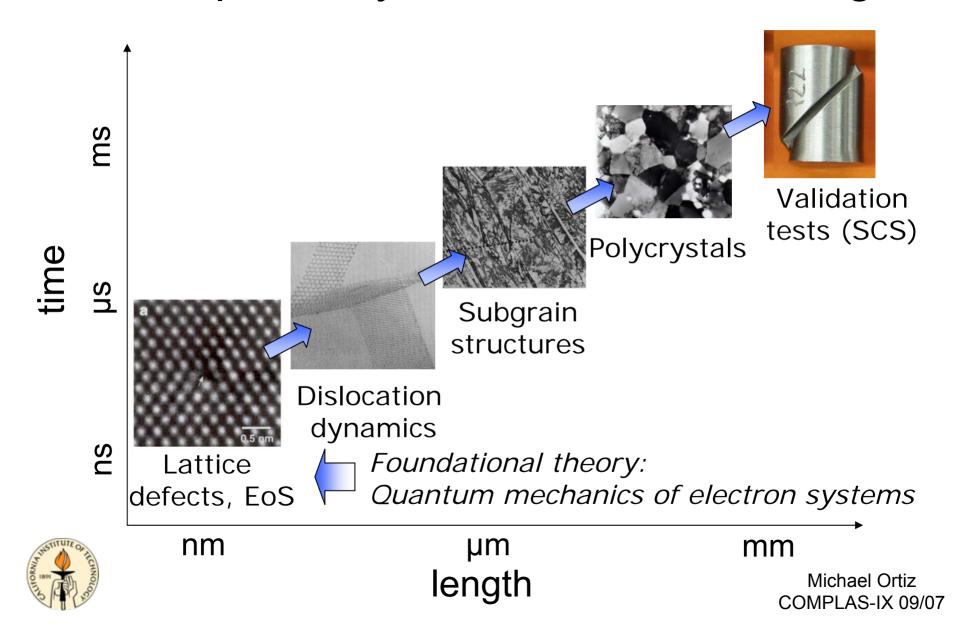
Electronic-structure calculations at macroscopic scales

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COMPLAS-IX
Barcelona, September 6, 2007

Metal plasticity – Multiscale modeling



Predicting Properties of Matter from Electronic Structure

- The quantum mechanics of electrons and ions lies at the foundation of a large part of low-energy physics, chemistry and biology
- The Born-Oppenheimer approximation: Decouples the electronic and nuclear motion, electrons respond instantaneously to any change in nuclear coordinates
- Time-independent Schrödinger equation for an isolated N-electron atomic or molecular system:

$$\widehat{H}\Psi = E\Psi$$

$$\hat{H} = \sum_{i=1}^{N} \left(-\frac{1}{2}\nabla_i^2\right) + \sum_{i=1}^{N} v(r_i) + \sum_{i< j}^{N} \frac{1}{r_{ij}}$$



Quantum mechanics and material properties

Quantum Mechanics of Many-Electron Systems.

By P. A. M. Dirac, St. John's College, Cambridge.

(Communicated by R. H. Fowler, F.R.S.—Received March 12, 1929.)

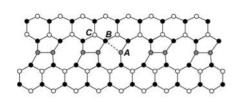
§ 1. Introduction.

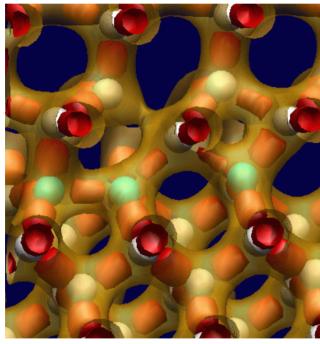
The general theory of quantum mechanics is now almost complete, the imperfections that still remain being in connection with the exact fitting in of the theory with relativity ideas. These give rise to difficulties only when high-speed particles are involved, and are therefore of no importance in the consideration of atomic and molecular structure and ordinary chemical reactions, in which it is, indeed, usually sufficiently accurate if one neglects relativity variation of mass with velocity and assumes only Coulomb forces between the various electrons and atomic nuclei. The underlying physical laws necessary for the mathematical theory of a large part of physics and the whole of chemistry are thus completely known, and the difficulty is only that the exact application of these laws leads to equations much too complicated to be soluble. It therefore becomes desirable that approximate practical methods of applying quantum mechanics should be developed, which can lead to an explanation of the main features of complex atomic systems without too much computation.

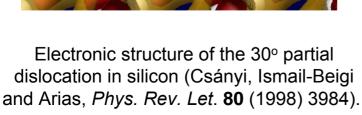


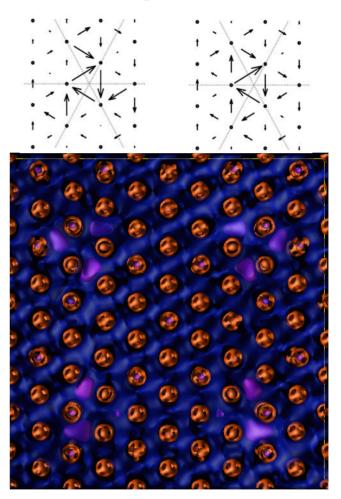
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Defective crystals – Supercells









Ab initio study of screw dislocations in Mo and Ta (Ismail-Beigi and Arias, Phys. Rev. Let. **84** (2000) 1499). Michael Ortiz COMPLAS-IX 09/07

Defective crystals – The chasm

- Because of computational cost, supercells limited to small sizes → Exceedingly large defect concentrations
- Often the objective is to predict bulk properties of defects:
 - Vacancies: cell size ~ 100 nm
 - Dislocation cores: cell size ~ 100 nm
 - Domain walls: cell size ~ 1 μm
 - Grain boundaries: cell size ~ 20 μm
- Small-cell calculations lead to discrepancies with experimental measurements!
- How can bulk properties of defects (>> million atom computational cells) be predicted from electronic structure calculations?



Density functional theory

• Theorem [Hohenberg-Kohn, 1964] The external potential v(r) is determined by the electron density

$$\rho(\mathbf{r}) = N \int |\Psi|^2 ds_1 dx_1 \dots x_N$$

- Corollary: $E[\rho] = T[\rho] + V_{ne}[\rho] + V_{ee}[\rho]$
- Theorem [Hohenberg-Kohn, 1964] $E_0 = \inf_{\rho} E[\rho]$
- Orbital-free DFT (OFDFT):

$$E[\rho] = \int \epsilon_{loc}(\mathbf{r}, \rho, \nabla \rho) d\mathbf{r} + \frac{1}{2} \int_{\Omega} \int_{\Omega} \frac{\rho(\mathbf{r})\rho(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|} d\mathbf{r} d\mathbf{r}'$$



$$T_s[\rho] + E_{xc}[\rho] + V_{ne}[\rho]$$

OFDFT – Real space formulation

Total energy functional:

$$E[\rho] = \int \epsilon_{loc}(\mathbf{r}, \rho, \nabla \rho) \, d\mathbf{r} + \frac{1}{2} \int_{\Omega} \int_{\Omega} \frac{\rho(\mathbf{r})\rho(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|} \, d\mathbf{r} \, d\mathbf{r}'$$
 finely oscillatory! nonlocal!

• Local Lagrangian form:
$$E[\rho] = \sup_{\phi \in H^1(\mathbf{R}^3)} L[\rho, \phi]$$

$$L[\rho, \phi] = \int \epsilon_{loc}(\mathbf{r}, \rho, \nabla \rho) d\mathbf{r}$$

$$-\frac{1}{8\pi}\int_{\Omega}|\nabla\phi(\mathbf{r})|^2\,d\mathbf{r}+\int_{\Omega}(\rho(\mathbf{r})+b(\mathbf{r}))\phi(\mathbf{r})\,d\mathbf{r}$$

pseudopotentials COMPLAS-IX 09/07

OFDFT – Real space formulation

- Enforce constraint $\rho > 0$ by setting $\rho = u^2$.
- Saddle-point problem:

$$\inf_{u\in H^1(\Omega)}\sup_{\phi\in H^1(\mathbb{R}^3)}L(u,\phi)$$
 subject to:
$$\int_{\Omega}u^2(r)dr=N$$

Theorem [BGKO] Let E[u] be the TF- λ W + LDA energy functional, $X = \{u \in H^1(\Omega), \|u\|_{L^2(\Omega)}^2 = N\}.$ Then E[u] has a minimum in X.



OFDFT – FE approximation

- Let $X_h \times Y_h$ be a sequence of finite-element subspaces of $H^1_0(\Omega) \times H^1(\mathbb{R}^3)$.
- Discrete problem: $F[u, \phi] \equiv$

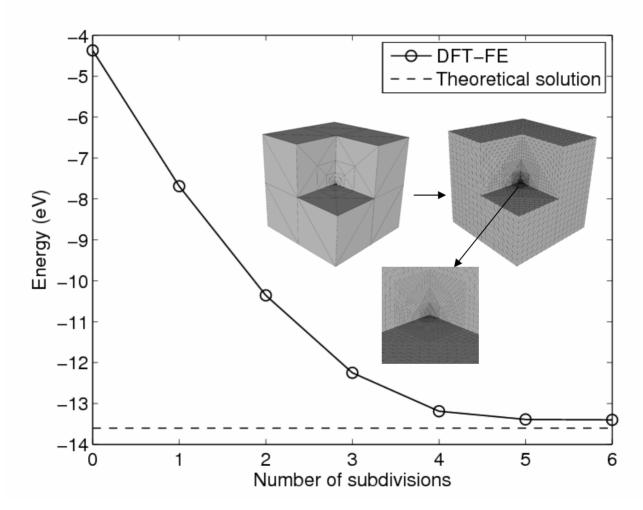
$$-\frac{1}{8\pi} \int_{\Omega} |\nabla \phi(\mathbf{r})|^2 d\mathbf{r} + \int_{\Omega} (u^2(\mathbf{r}) + b(\mathbf{r})) \phi(\mathbf{r}) d\mathbf{r}$$

$$F_h[u,\phi] = \begin{cases} F[u,\phi], & \text{if } \phi \in Y_h \\ -\infty, & \text{otherwise.} \end{cases}$$

$$E_h[u] = \begin{cases} E_{loc}[u] + \sup_{\phi} F_h[u, \phi], & \text{if } u \in X_h \\ +\infty, & \text{otherwise.} \end{cases}$$

Theorem [BGKO] Γ -lim $_{h\to 0}$ $E_h=E$, inf $E_h\to E_0$.

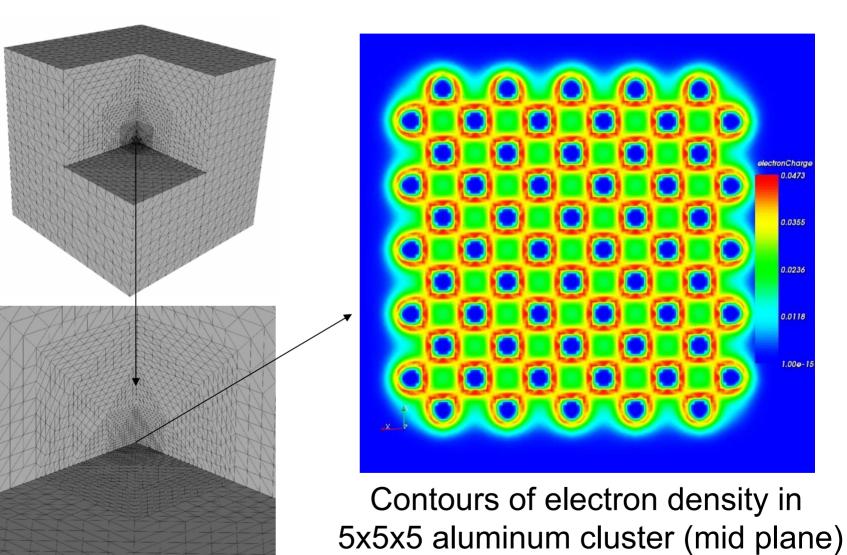
Convergence test – Hydrogen atom





Energy of hydrogen atom as a function of number of subdivisions of initial mesh

Example – Aluminum nanoclusters





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0.0355

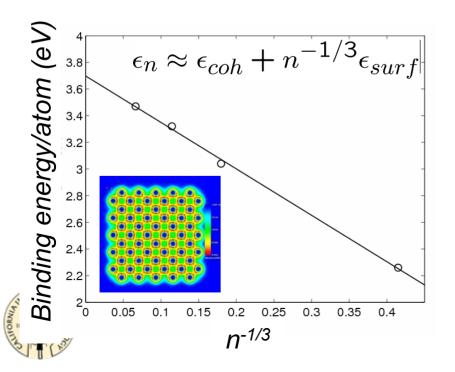
0.0236

0.0118

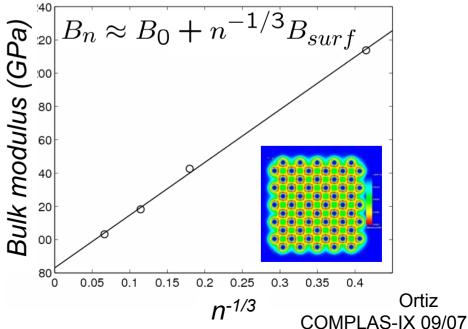
1.00e-1

Example – Aluminum nanoclusters

Property	DFT-FE	KS-LDA ^a	Experiments ^b
Lattice parameter (a.u.)	7.42	7.48	7.67
Cohesive energy (eV)	3.69	3.67	3.4
Bulk modulus (Gpa)	83.1	79.0	74.0



a/ Goodwin et al. (1990), Gaudion et al. (2002)b/ Brewer (1997), Gschneider (1964)



OFDFT – Coarse-graining

- Real-space formulation and finite-element approximation
 → Nonperiodic, unstructured, OFDFT calculations
- However, calculations are still expensive:
 9x9x9 cluster = 3730 atoms required 10,000 CPU hours!
- Isolated defects: All-atom calculations are unduly wasteful, electronic structure away from the defects is nearly identical to that of a uniformly deformed lattice
- Objective: Model reduction away from defects
- General approach (QC-OFDFT):
 - Derive a real space, nonperiodic, formulation of OFDFT $\sqrt{}$
 - Effect a quasi-continuum¹ (QC) model reduction
- Challenge: Subatomic oscillations and lattice scale modulations of electron density and electrostatic potential



QC/OFDFT – Multigrid hierarchy

Nuclear positions:

$$\mathbf{R} \in \mathbb{R}^{3M} \equiv Z$$

Equilibrium problem:

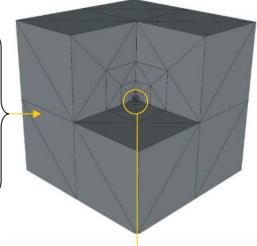
$$\inf_{\boldsymbol{R}\in Z}E_{0}[\boldsymbol{R}],$$

$$E_0[\mathbf{R}] = \inf_{u} \sup_{\phi} E[u, \phi]$$

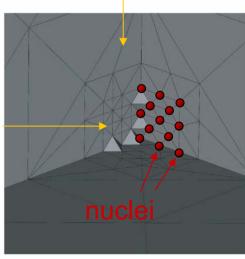
• Reduced problem:

$$\begin{cases} \inf_{\boldsymbol{R} \in Z_h} E_0[\boldsymbol{R}] \\ Z_h = \mathbb{R}^{3M_h}, M_h \ll M \end{cases}$$

coarse resolution, nuclei in interpolated positions



atomic resolution, nuclei in arbitrary positions



Coarse grid

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QC/OFDFT – Multigrid hierarchy

• Predictor/corrector¹:

$$\rho_h = \rho_h^0 + \rho_h^c$$

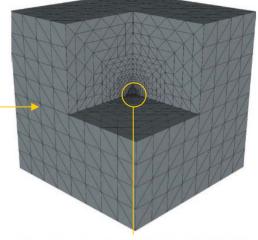
$$\phi_h = \phi_h^0 + \phi_h^c$$

$$\uparrow$$

$$\uparrow$$

$$\uparrow$$
 predictor corrector

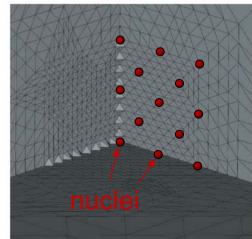
coarse resolution, slowlyvarying correction¹



 Predictor: Local Cauchy-Born field (LQC/OFDFT)² defined everywhere

subatomic resolution, rapidly-varying correction

 Corrector: Interpolated on intermediate grid



Intermediate grid

¹Blanc, LeBris, Lions, *ARMA*, **164** (2002) 341 ²Fago el al., *Phys. Rev.*, **B70** (2004) 100102(R)

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QC/OFDFT – Multigrid hierarchy

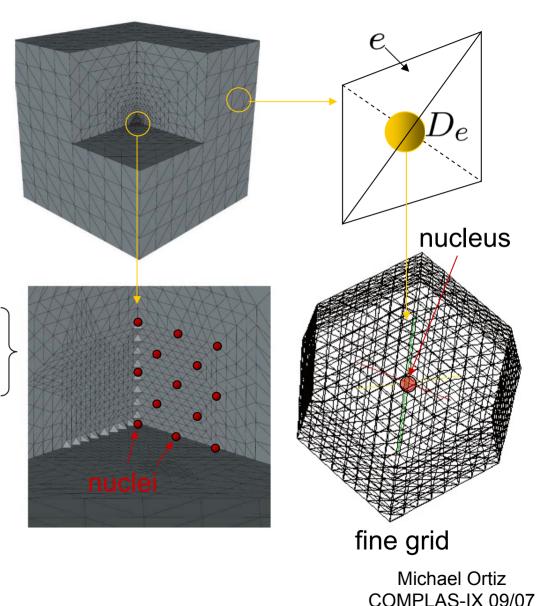
• Element quadrature:

$$\int_{e} f(\mathbf{r}) d\mathbf{r} \approx |e| \langle f \rangle_{D_{e}}$$

Quadrature domain:

$$D_e = \min \left\{ egin{array}{l} ext{atomic cell} \ ext{element } e \end{array}
ight\}$$

• $\langle f \rangle_{D_e}$ evaluated using a fine grid over D_e

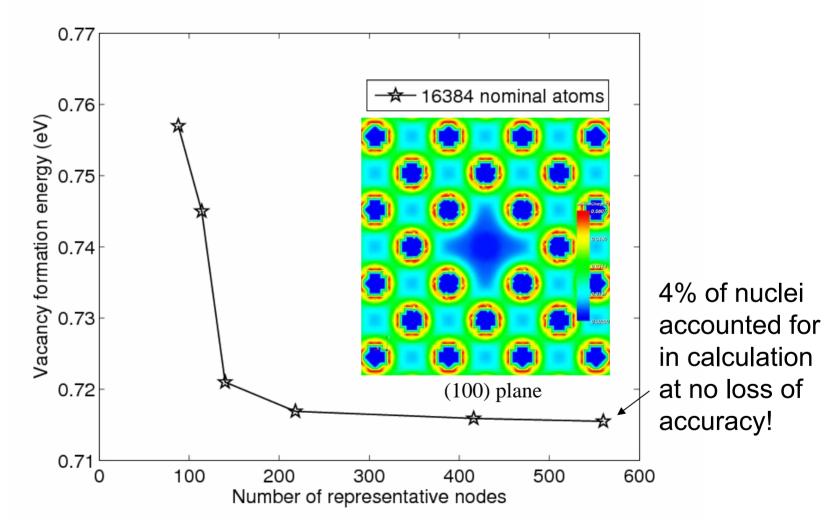


QC/OFDFT – Attributes

- The overall complexity of the method is set by the size of the intermediate mesh (interpolation of ρ_h , φ_h)
- All approximations are numerical: interpolation of fields, numerical quadrature
- No spurious physics is introduced: OFDFT is the sole input to the model
- A converged solution obtained by this scheme is a solution of OFDFT
- Coarse graining is seamless, unstructured, adaptive: no periodicity, no interfaces
- Fully-resolved OFDFT and continuum finite elasticity are obtained as extreme limits
- Million-atom OFDFT calculations possible at no significant loss of accuracy



QC/OFDFT convergence – Al vacancy

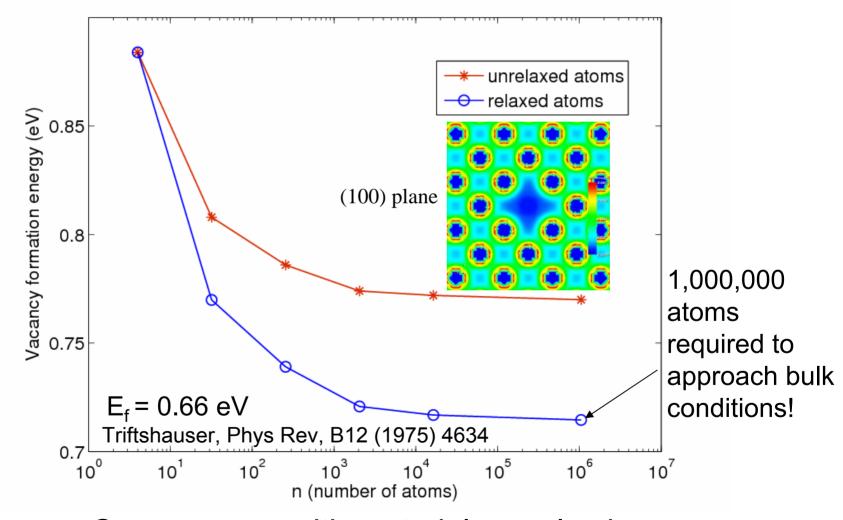




Convergence of QC reduction

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QC/OFDFT convergence – Al vacancy





Convergence with material sample size

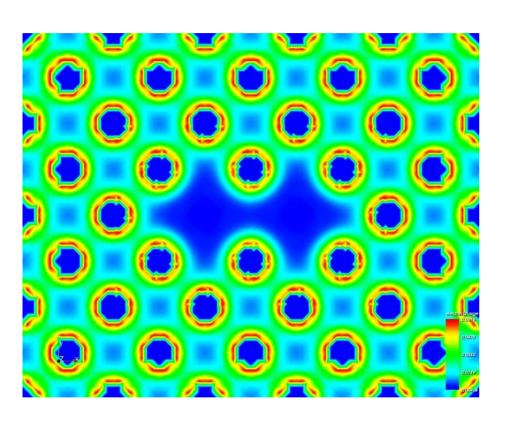
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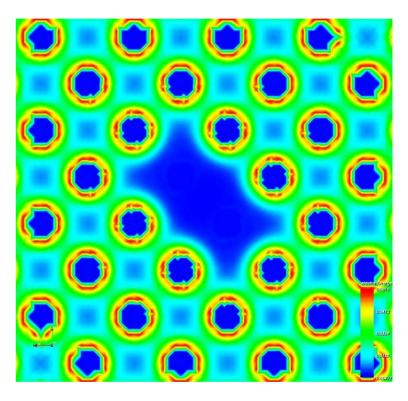
QC/OFDFT convergence – Al vacancy

- QC reduction converges rapidly:
 - 16,384-atom sample: ~200 representative atoms required for ostensibly converged vacancy formation energy.
 - 1,000,000-atom sample: ~1,017 representative atoms and ~
 450,000 electron-density nodes give vacancy formation energy within ~0.01 eV of converged value
- Vacancies have long-range elastic field and convergence with respect to sample size is slow: ~1,000,000 atom sample required to attain singlevacancy formation energy!
- What can we learn from large cell sizes?
 - Case study 1: Di-vacancies in aluminum
 - Case studey 2: Prismatic loops in aluminum



Case study 1 – Di-vacancies in Al





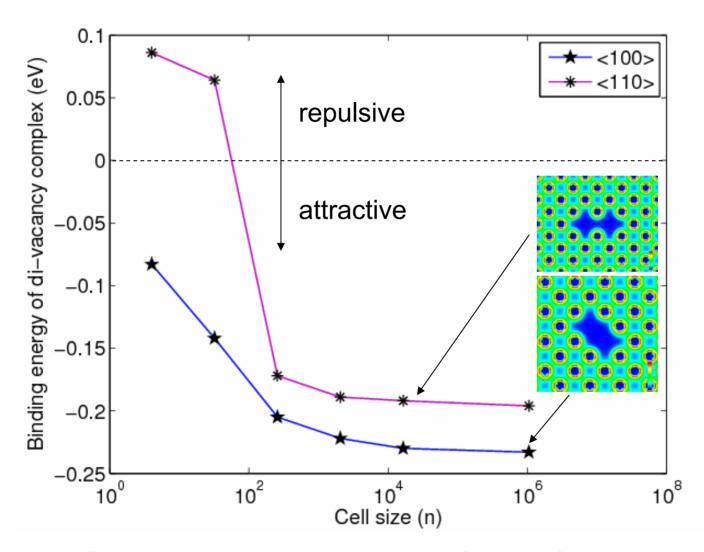
Di-vacancy along <100>

Di-vacancy along <110>



Core electronic structure

Case study 1 – Di-vacancies in Al



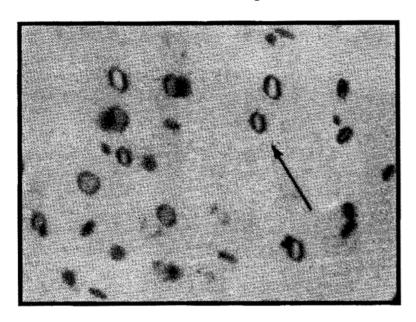


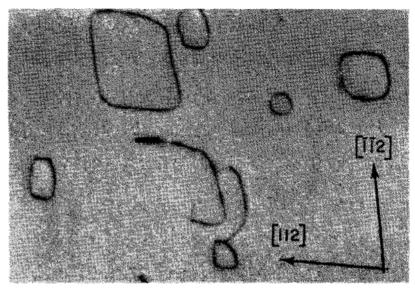
Binding energy vs. material sample size

Case study 1 – Di-vacancies in Al

- Calculations evince a strong cell-size effect: binding energy changes from repulsive at large concentrations to attractive at bulk concentrations
- Sample sizes containing > 1,000,000 atoms must be used in order to approach bulk conditions
- Di-vacancy binding energies are computed to be:
 -0.19 eV for <110> di-vacancy; -0.23 eV for <100> di-vacancy
- Agreement with experimental values: -0.2 to -0.3 eV (Ehrhart et al., 1991; Hehenkamp, 1994)
- Small-cell size values consistent with previous DFT calculations (Carling et al., 2000; Uesugi et. al, 2003):
 +0.05 eV for <110> di-vacancy; -0.04 eV for <100> di-vacancy
 - No discrepancy between theory and experiment, only strong vacancy-concentration effect!

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Prismatic dislocation loops formed by condensation of vacancies in quenched aluminum

Kulhmann-Wilsdorff and Kuhlmann,

J. Appl. Phys., 31 (1960) 516.

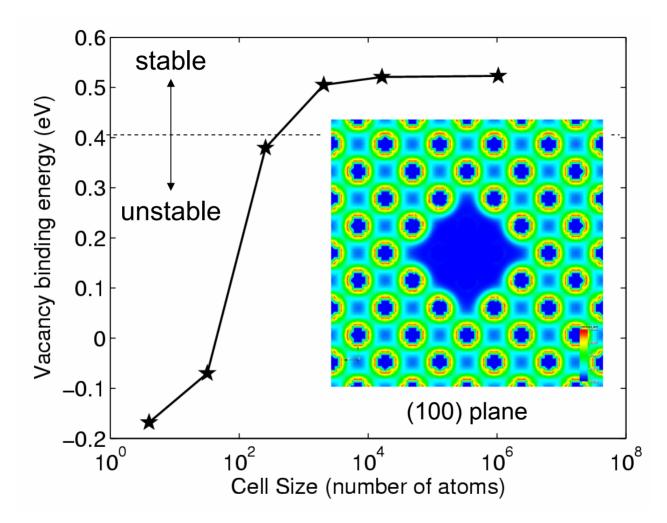
Prismatic dislocation loops formed by condensation of vacancies in quenched Al-05%Mg

Takamura and Greensfield,

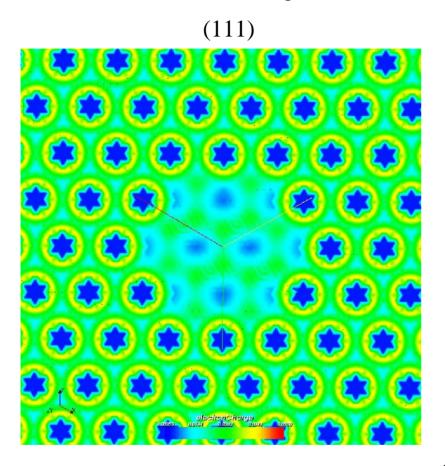
J. Appl. Phys., 33 (1961) 247.

Prismatic dislocation loops also in irradiated materials
 Loops smaller than 50 nm undetectable: Nucleation
 mechanism? Vacancy condensation?

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Quad-vacancy binding energy vs. material sample size



(001)

Non-collapsed configuration Binding energy = -0.88 eV 1/2<110> prismatic loop Binding energy = -1.57 eV



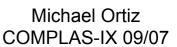
Stability of hepta-vacancy

- Growth of planar vacancy clusters is predicted to be energetically favorable for sufficiently small concentrations
- Elucidation of relevant conditions requires large cell-size calculations
- Vacancy clustering and subsequent collapse is a possible mechanism for formation of prismatic dislocation loops
- Prismatic loops as small as those formed from heptavacancies are stable!



Concluding remarks

- Predictive multiscale models of materials require:
 - physics-based multiscale modeling: QM foundational theory
 - Approximations that do not compromise the physics and that introduce controllable errors and the possibility of convergence
- Finite elements provide an ideal basis for real-space non-periodic formulations of OFDFT
- Behavior of material samples may change radically with size (concentration): Small samples may not be representative of bulk behavior
- Need electronic structure calculations at macroscopic scales: Quasi-continuum OFDFT (QC/OFDFT)
- Outlook: Application to general materials requires extension to Kohn-Sham DFT...



Concluding remarks

Gavini V, Knap J, Bhattacharya K, Ortiz, M, Non-periodic finite element formulation of orbital-free density functional theory, Journal of the Mechanics and Physics of Solids, **55** (4): 669-696 April 2007.

Gavini V, Bhattacharya K, Ortiz M, Quasi-continuum orbitalfree density-functional theory: A route to multi-million atom non-periodic DFT calculation, Journal of the Mechanics and Physics of Solids, **55** (4): 697-718 April 2007.

